

MC74HC245A

Octal 3-State Noninverting Bus Transceiver

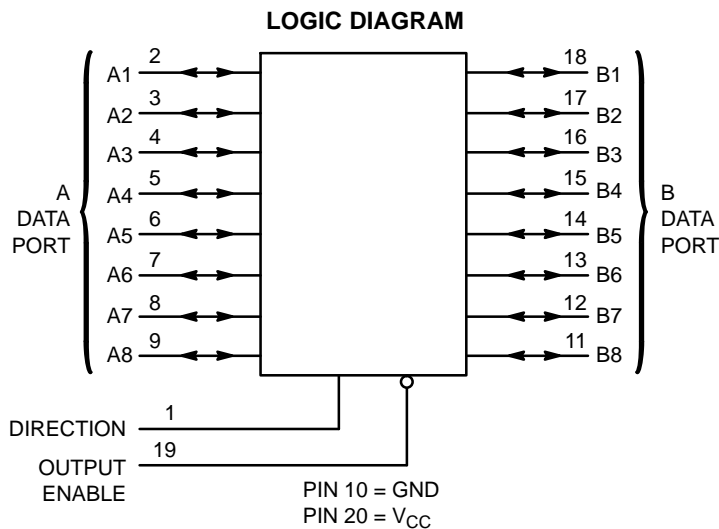
High-Performance Silicon-Gate CMOS

The MC74HC245A is identical in pinout to the LS245. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

The HC245A is a 3-state noninverting transceiver that is used for 2-way asynchronous communication between data buses. The device has an active-low Output Enable pin, which is used to place the I/O ports into high-impedance states. The Direction control determines whether data flows from A to B or from B to A.

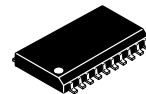
Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 308 FETs or 77 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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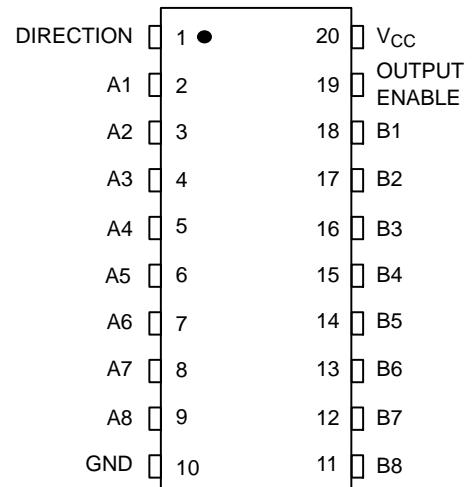


SOIC-20
DW SUFFIX
CASE 751D

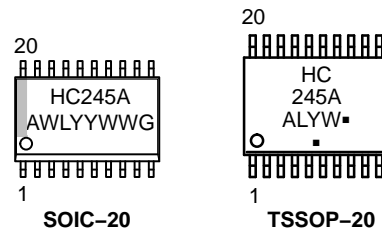


TSSOP-20
DT SUFFIX
CASE 948E

PIN ASSIGNMENT



MARKING DIAGRAMS



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MC74HC245A

FUNCTION TABLE

Control Inputs		Operation
Output Enable	Direction	
L	L	Data Transmitted from Bus B to Bus A
L	H	Data Transmitted from Bus A to Bus B
H	X	Buses Isolated (High-Impedance State)

X = don't care

MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	-0.5 to +7.0	V
V_{IN}	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V_{OUT}	DC Output Voltage (Note 2)	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 35	mA
I_{OUT}	DC Output Sink Current	± 35	mA
I_{CC}	DC Supply Current per Supply Pin	± 75	mA
I_{GND}	DC Ground Current per Ground Pin	± 75	mA
T_{STG}	Storage Temperature Range	-65 to +150	$^{\circ}C$
T_L	Lead Temperature, 1 mm from Case for 10 Seconds	260	$^{\circ}C$
T_J	Junction Temperature Under Bias	+150	$^{\circ}C$
θ_{JA}	Thermal Resistance	SOIC TSSOP 96 128	$^{\circ}C/W$
P_D	Power Dissipation in Still Air at 85 $^{\circ}C$	SOIC TSSOP 500 450	mW
MSL	Moisture Sensitivity	Level 1	
F_R	Flammability Rating	Oxygen Index: 30% to 35% UL 94 V-0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5) > 2000 > 200 > 1000	V
$I_{LATCHUP}$	Latchup Performance	Above V_{CC} and Below GND at 85 $^{\circ}C$ (Note 6)	± 300 mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 20 ounce copper trace with no air flow.
2. I_O absolute maximum rating must be observed.
3. Tested to EIA/JESD22-A114-A.
4. Tested to EIA/JESD22-A115-A.
5. Tested to JESD22-C101-A.
6. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	-55	+125	$^{\circ}C$
t_r, t_f	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 V$ $V_{CC} = 4.5 V$ $V_{CC} = 6.0 V$	0 1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

MC74HC245A

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				-55 to 25°C	≤ 85°C	≤ 125°C	
V _{IH}	Minimum High-Level Input Voltage	V _{out} = V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	1.5	1.5	1.5	V
			3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V I _{out} ≤ 20 μA	2.0	0.5	0.5	0.5	V
			3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} I _{out} ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
			V _{in} = V _{IH} I _{out} ≤ 2.4 mA I _{out} ≤ 6.0 mA I _{out} ≤ 7.8 mA	3.0	2.48	2.34	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IL} I _{out} ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
			V _{in} = V _{IL} I _{out} ≤ 2.4 mA I _{out} ≤ 6.0 mA I _{out} ≤ 7.8 mA	3.0	0.26	0.33	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I _{oZ}	Maximum Three-State Leakage Current	Output in High-Impedance State V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	6.0	±0.5	±5.0	±10	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4.0	40	160	μA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			-55 to 25°C	≤ 85°C	≤ 125°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to B, B to A (Figures 1 and 3)	2.0	75	95	110	ns
		3.0	55	70	80	
		4.5	15	19	22	
		6.0	13	16	19	
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Direction or Output Enable to A or B (Figures 2 and 4)	2.0	110	140	165	ns
		3.0	90	110	130	
		4.5	22	28	33	
		6.0	19	24	28	
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to A or B (Figures 2 and 4)	2.0	110	140	165	ns
		3.0	90	110	130	
		4.5	22	28	33	
		6.0	19	24	28	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0	60	75	90	ns
		3.0	23	27	32	
		4.5	12	15	18	
		6.0	10	13	15	
C _{in}	Maximum Input Capacitance (Pin 1 or Pin 19)	-	10	10	10	pF
C _{out}	Maximum Three-State I/O Capacitance (I/O in High-Impedance State)	-	15	15	15	pF
C _{PD}	Power Dissipation Capacitance (Per Transceiver Channel) (Note 7)	Typical @ 25°C, V _{CC} = 5.0 V			pF	
		40				

7. Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

MC74HC245A

ORDERING INFORMATION

Device	Package	Shipping†
MC74HC245ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
NLV74HC245ADWG*	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC245ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
NLV74HC245ADWR2G*	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC245ADTG	TSSOP-20 (Pb-Free)	75 Units / Rail
NLV74HC245ADTG*	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74HC245ADTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel
NLV74HC245ADTR2G*	TSSOP-20 (Pb-Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

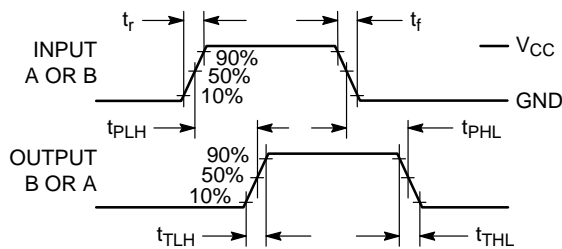


Figure 1. Switching Waveform

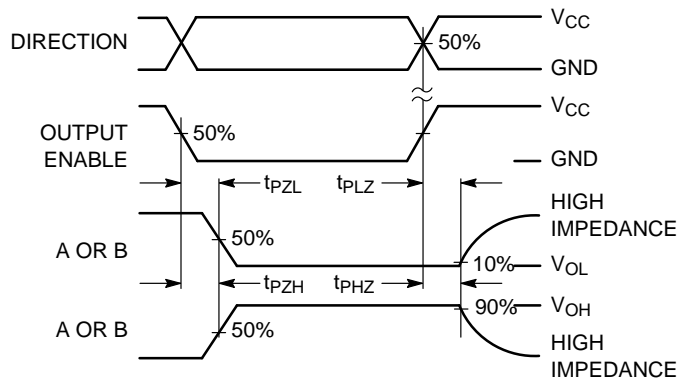
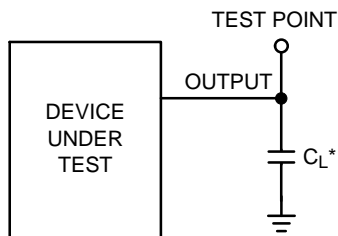
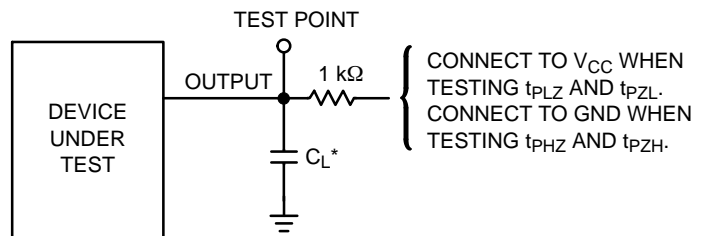


Figure 2. Switching Waveform



*Includes all probe and jig capacitance

Figure 3. Test Circuit



*Includes all probe and jig capacitance

Figure 4. Test Circuit

MC74HC245A

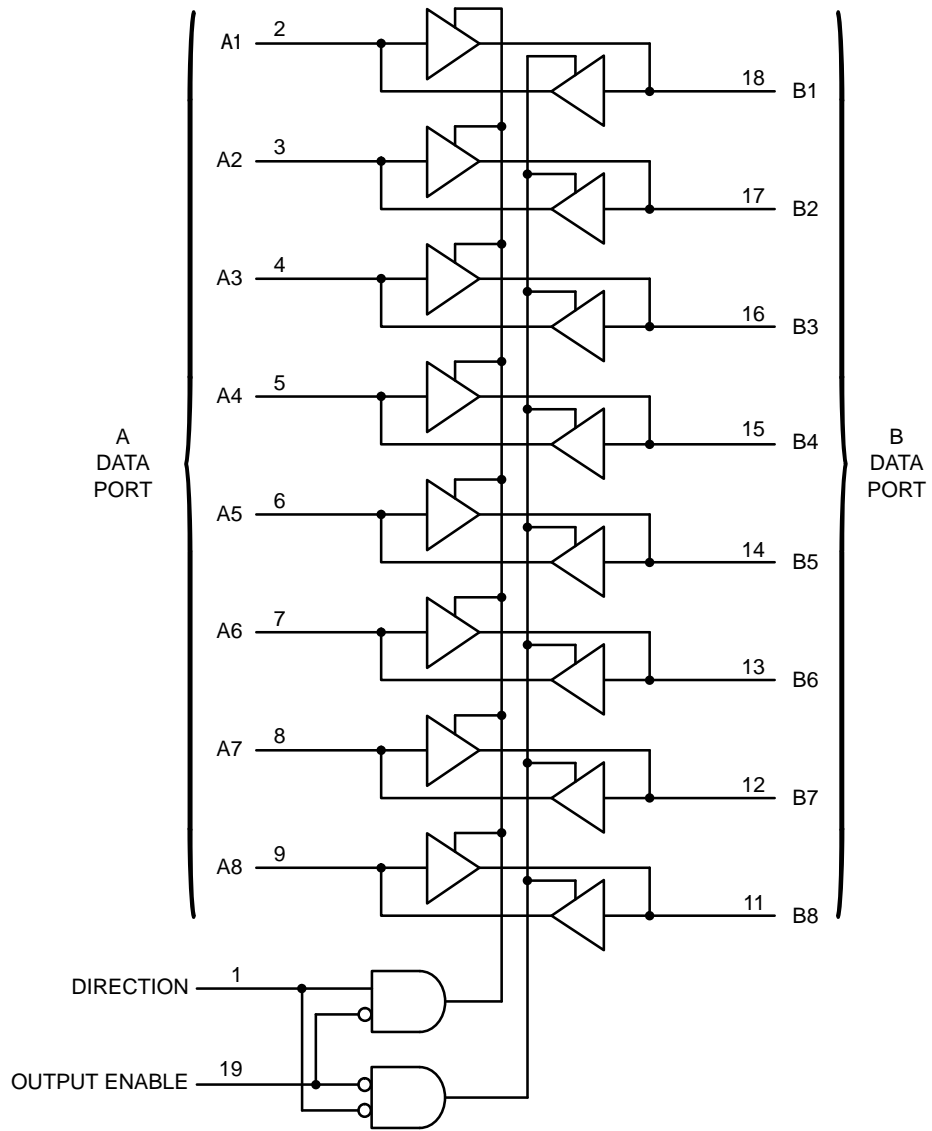


Figure 5. Expanded Logic Diagram

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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SCALE 1:1

SOIC-20 WB
CASE 751D-05
ISSUE H

DATE 22 APR 2015



NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

RECOMMENDED
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



TSSOP-20 WB
CASE 948E
ISSUE D

DATE 17 FEB 2016

SCALE 2:1



NOTES:

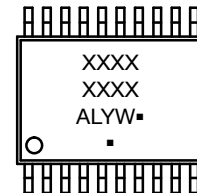
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°



SOLDERING FOOTPRINT

GENERIC MARKING DIAGRAM*



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.



DIMENSIONS: MILLIMETERS

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